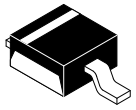
Surface Mount Schottky Power Rectifier

POWERMITE®
Power Surface Mount Package

MBRM120ET1G, NRVBM120ET1G, MBRM120ET3G, NRVBM120ET3G

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES, 20 VOLTS



POWERMITE
CASE 457
STYLE 1

The Schottky POWERMITE® employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop−reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the POWERMITE® has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC−DC and DC−DC converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

Features

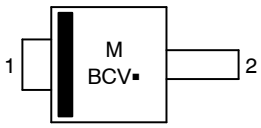
- Low Profile − Maximum Height of 1.1 mm
- Small Footprint − Footprint Area of 8.45 mm2
- Low V_F Provides Higher Efficiency and Extends Battery Life
- ESD Ratings:
  - ♦ Machine Model = C (> 400 V)
  - ♦ Human Body Model = 3B (> 16,000 V)
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink
- AEC−Q101 Qualified and PPAP Capable
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb−Free*

Mechanical Characteristics

- POWERMITE® is JEDEC Registered as DO−216AA
- Case: Molded Epoxy
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 16.3 mg (approximately)
- Lead and Mounting Surface Temperature for Soldering Purposes 260°C Maximum for 10 Seconds

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



BCV = Device Code
M = Date Code
▪ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
MBRM120ET1G	POWERMITE (Pb−Free)	3,000 / Tape & Reel
NRVBM120ET1G	POWERMITE (Pb−Free)	3,000 / Tape & Reel
MBRM120ET3G	POWERMITE (Pb−Free)	12,000 / Tape & Reel

DISCONTINUED (Note 1)

NRVBM120ET3G	POWERMITE (Pb−Free)	12,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	20	V
I_O	Average Rectified Forward Current (At Rated V_R, T_C = 130°C)	1.0	A
I_{FRM}	Peak Repetitive Forward Current (At Rated V_R, Square Wave, 20 kHz, T_C = 135°C)	2.0	A
I_{FSM}	Non−Repetitive Peak Surge Current (Non−Repetitive peak surge current, halfwave, single phase, 60 Hz)	50	A
T_{stg}	Storage Temperature	−65 to 150	°C
T_J	Operating Junction Temperature	−65 to 150	°C
dv/dt	Voltage Rate of Change (Rated V_R, T_J = 25°C)	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Unit
R_{tjl} R_{tjtab} R_{tja}	Thermal Resistance − Junction−to−Lead (Anode) (Note 1) Thermal Resistance − Junction−to−Tab (Cathode) (Note 1) Thermal Resistance − Junction−to−Ambient (Note 1)	35 23 277	°C/W

1. Mounted with minimum recommended pad size, PC Board FR4, See Figures 9 and 10.

ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Value		Unit
V_F	Maximum Instantaneous Forward Voltage (Note 2), See Figure 2	**T_J = 25°C**	**T_J = 100°C**	V
	(I_F = 0.1 A) (I_F = 1.0 A) (I_F = 2.0 A)	0.455 0.530 0.595	0.360 0.455 0.540	
I_R	Maximum Instantaneous Reverse Current (Note 2), See Figure 4	**T_J = 25°C**	**T_J = 100°C**	μA
	(V_R = 20 V) (V_R = 10 V) (V_R = 5.0 V)	10 1.0 0.5	1600 500 300	

2. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2%.

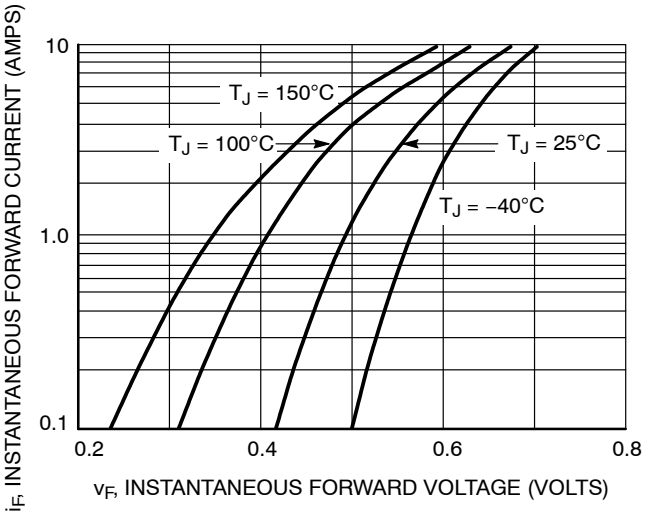


Figure 1. Typical Forward Voltage

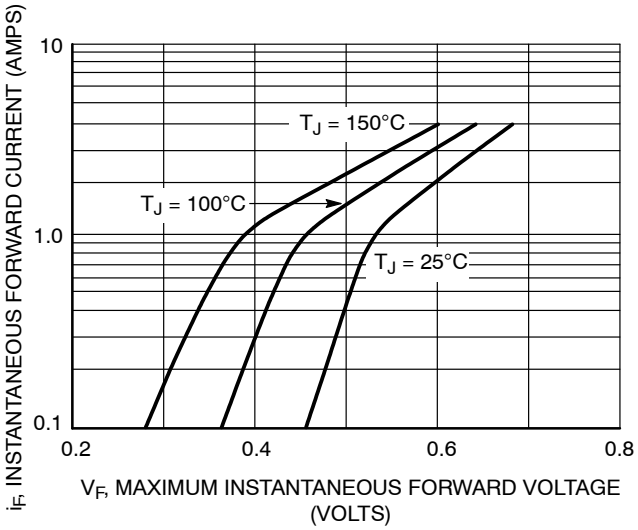


Figure 2. Maximum Forward Voltage

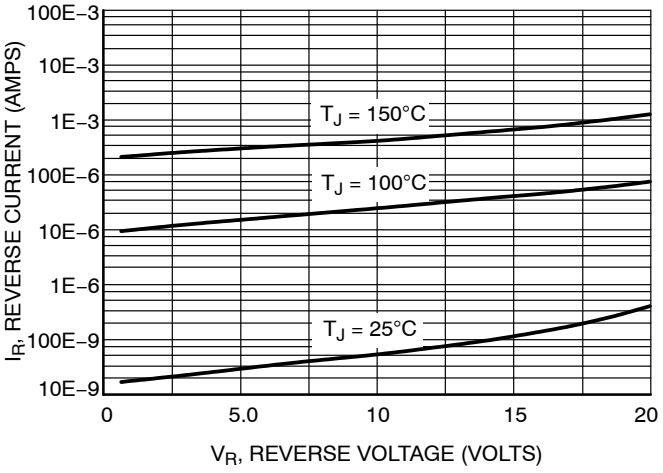


Figure 3. Typical Reverse Current

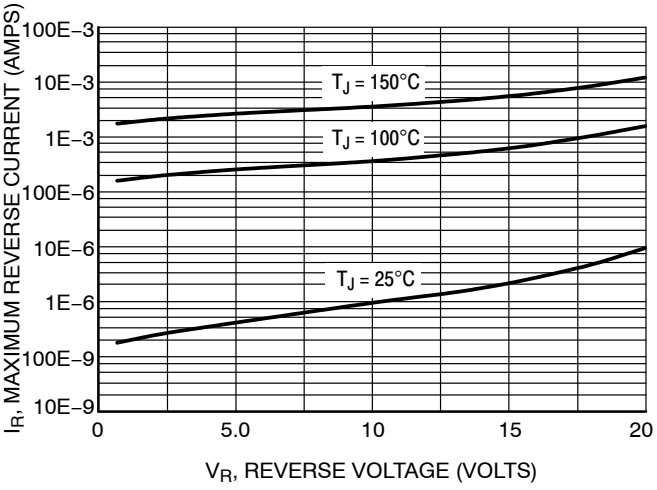


Figure 4. Maximum Reverse Current

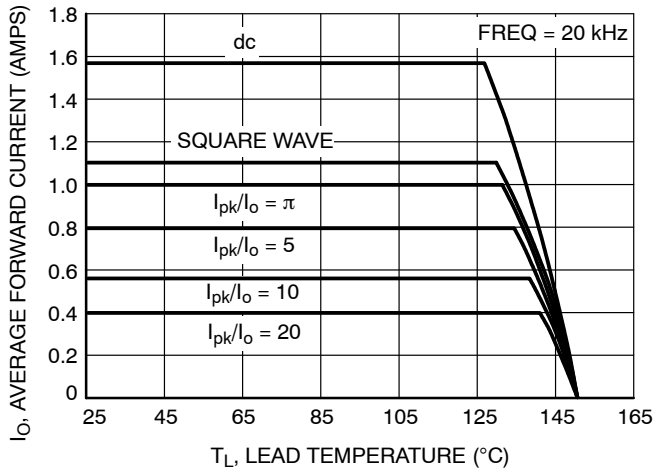


Figure 5. Current Derating

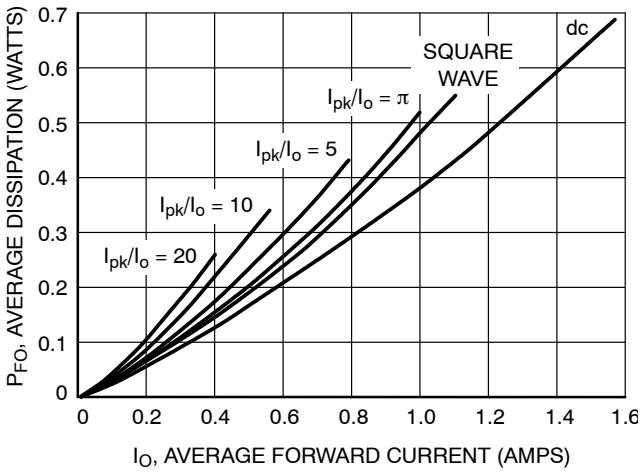


Figure 6. Forward Power Dissipation

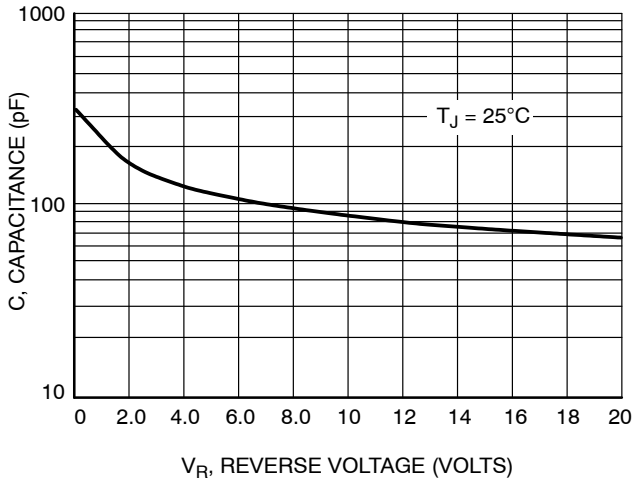


Figure 7. Capacitance

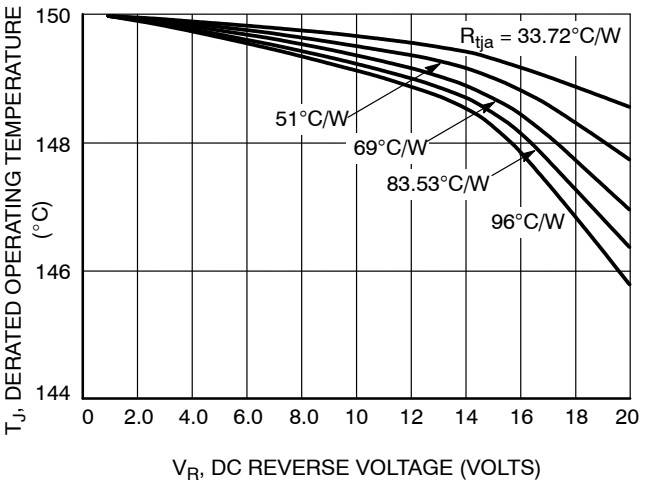


Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

$r(t)$ = thermal impedance under given conditions,
Pf = forward power dissipation, and
Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

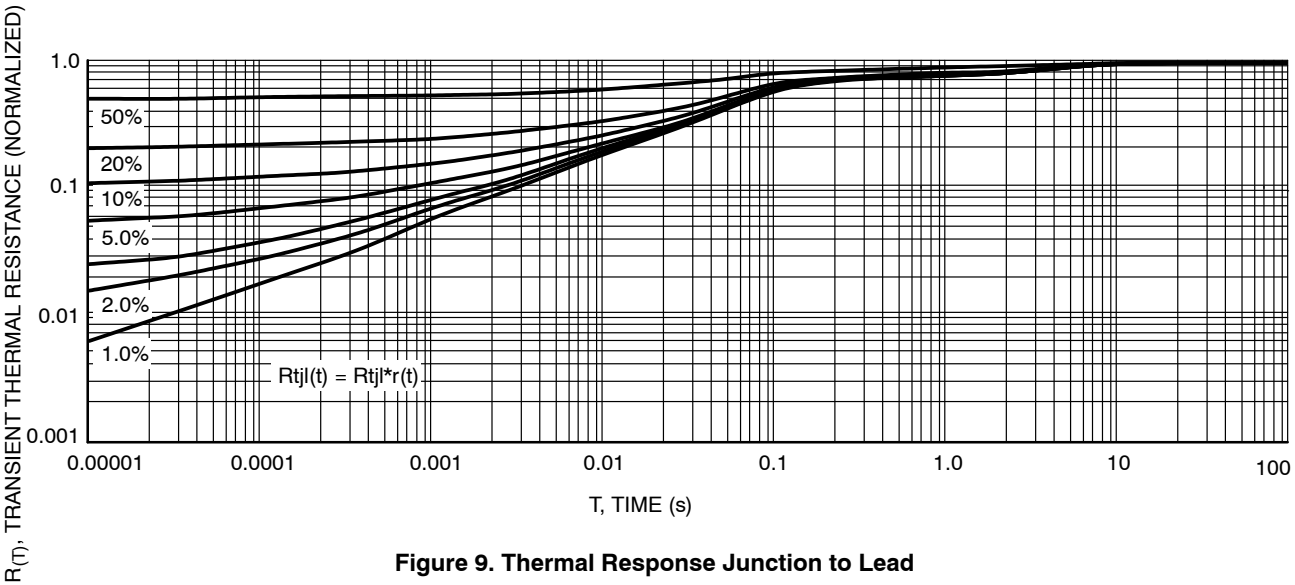


Figure 9. Thermal Response Junction to Lead

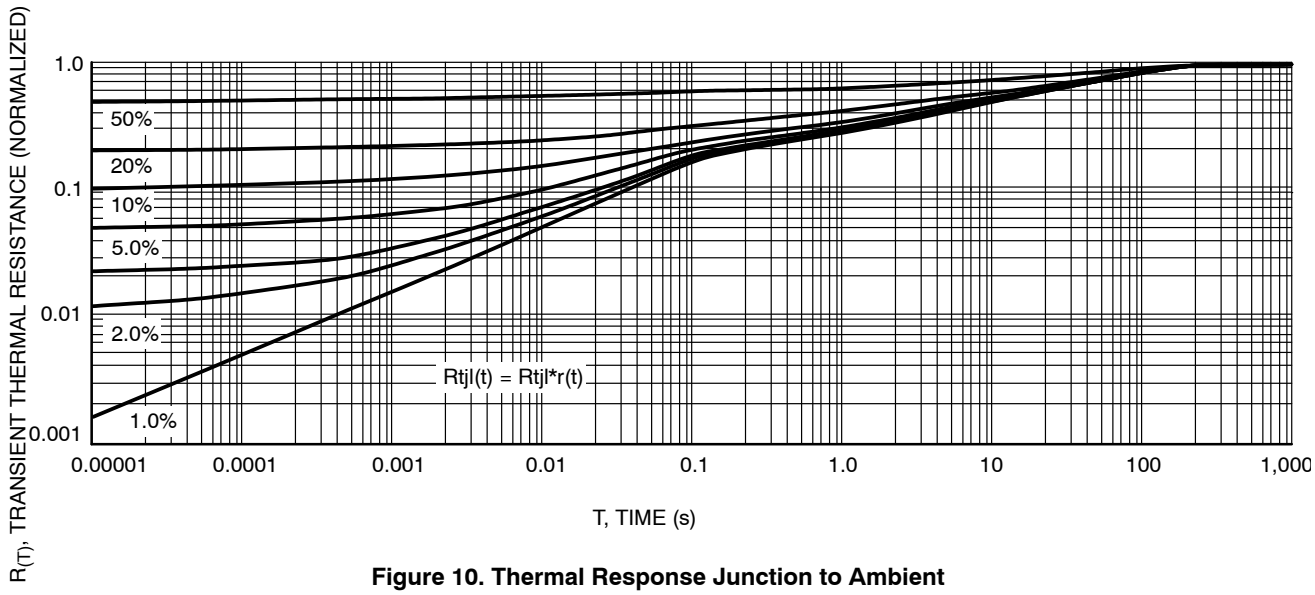


Figure 10. Thermal Response Junction to Ambient

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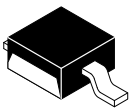
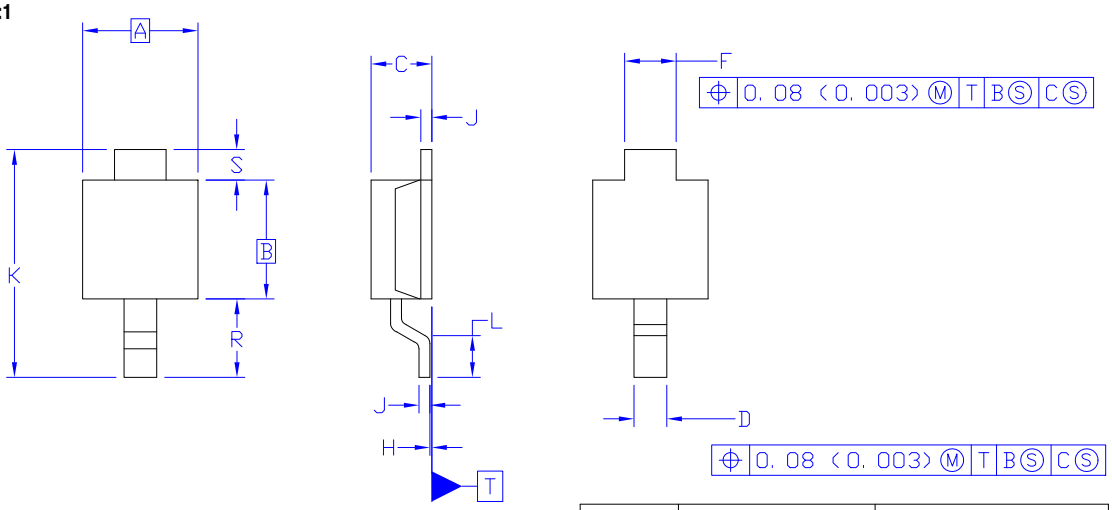
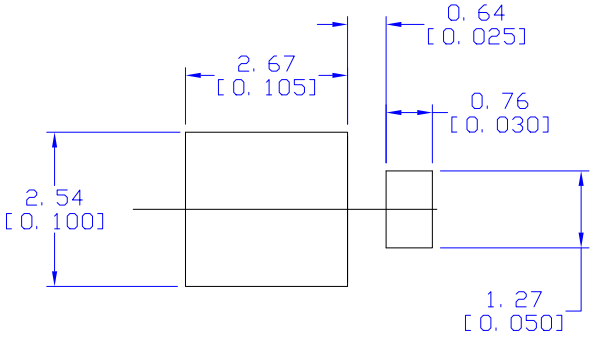


SCALE 4:1

POWERMITE
CASE 457
ISSUE G

DATE 12 JAN 2022





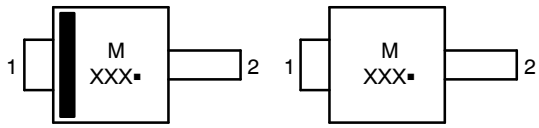
RECOMMENDED
MOUNTING FOOTPRINT

DIM	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.75	2.05	0.069	0.081
B	1.75	2.18	0.069	0.086
C	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
H	−0.05	0.10	−0.002	0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50 REF		0.019 REF	

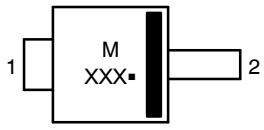
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.

GENERIC
MARKING DIAGRAMS*



STYLE 1 **STYLE 2**



STYLE 3

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE OR CATHODE
2. CATHODE OR ANODE
(BI−DIRECTIONAL)

STYLE 3:
PIN 1. ANODE
2. CATHODE

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